



1           **IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

2           Application Serial No. .... 09/292,132  
3           Filing Date ..... April 14, 1999  
4           Inventorship ..... Salman Akram et al.  
5           Assignee ..... Micron Technology, Inc.  
6           Group Art Unit ..... 2812  
7           Examiner ..... S. Mulpuri  
8           Attorney's Docket No. .... MI22-1171  
9           Title ..... Methods of Forming a Transistor Gate

10           **RESPONSE TO JUNE 5, 2000 OFFICE ACTION**

11           To:       Assistant Commissioner for Patents  
12                   Washington, D.C. 20231  
13           From:     James D. Shaurette (Tel. 509-624-4276; Fax 509-838-3424)  
14                   Wells, St. John, Roberts, Gregory & Matkin P.S.  
15                   601 West First Avenue, Suite 1300  
16                   Spokane, WA 99201-3828

17           Sir:

18           Responsive to the Office Action dated June 5, 2000, Applicant  
19           amends and remarks as follows [unless otherwise indicated, deletions are  
20           bracketed, additions are underlined]:

21           **AMENDMENTS**

22           **In the Claims**

23           Please amend the following claims:

24           *RECEIVED  
AUG 14 2000  
TECHNOLOGY CENTER 2800*